06/11/03

200 3065687

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
5 December 2002 (05.12.2002)

PCT

162162

(10) International Publication Number
WO 02/097878 A3

(51) International Patent Classification[7]: H01L 21/66, G01B 11/06

(21) International Application Number: PCT/US02/12827

(22) International Filing Date: 2 April 2002 (02.04.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/865,286 25 May 2001 (25.05.2001) US

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(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZM, ZW.

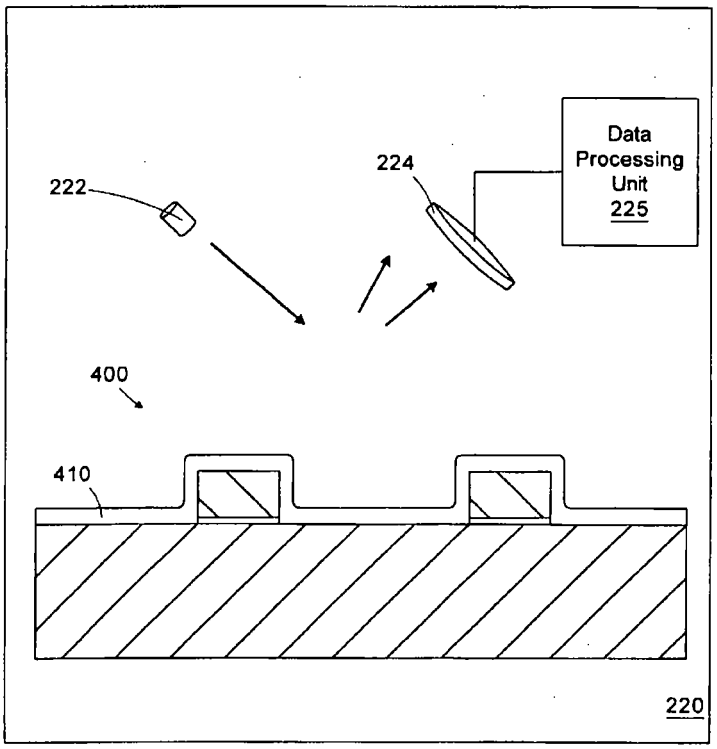
(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

(88) Date of publication of the international search report:
16 October 2003

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD AND APPARATUS FOR DETERMINING PROCESS LAYER CONFORMALITY



(57) Abstract: A method for determining conformality of a process layer (410) includes providing a wafer (205) having a grating structure (400) and a process layer (410) formed over the grating structure (400); illuminating at least a portion of the process layer (410) overlying the grating structure (400) with a light source (222); measuring light reflected from the illuminated portion of the grating structure (400) and the process layer (410) to generate a reflection profile; and determining conformality of the process layer (410) based on the reflection profile. A metrology tool (220) adapted to receive a wafer (205) having a grating structure (400) and a process layer (410) formed over the grating structure (400) includes a light source (222), a detector (224), and a data processing unit (225). The light source (222) is adapted to illuminate at least a portion of the process layer (410) overlying the grating structure (400). The detector (224) is adapted to measure light reflected from the illuminated portion of the grating structure (400) and the process layer (410) to generate a reflection profile. The data processing unit (225) is adapted to determine conformality of the process layer (410) based on the generated reflection profile.

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